

U.S.S.N. 10,798,960

Claim Amendments

Please amend claims 1, 2, 4, 5, 8, 15-17, and 21 as follows:

Please cancel claims 31-43 as follows:

Please add new claims 44-49 as follows:

Listing of Claims

1. (currently amended) A method for improving charge mobility in a MOSFET device comprising the steps of:

providing a first gate with a first semiconductor conductive type and a second gate with a second semiconductor conductive type overlying a substrate;

forming a first strained layer with a first type of stress overlying said first gate including gate sidewall portions; and,

forming a second strained layer with a second type of stress overlying said second gate including gate sidewall portions.

2. (currently amended) The method of claim 1, further comprising the step of transferring the first stress type from the first strained layer to the first gate and the second stress type from the second strained layer to the second gate, said transfer comprising an annealing process.

3. (original) The method of claim 1, further comprising the step of removing the first and second strained layers.

4. (currently amended) The method of claim 1, wherein an oxide layer is formed over the first and second gates including gate sidewall portions ~~prior to the steps of forming a~~ and underlying first and second strained layers.

5. (currently amended) The method of claim 1, wherein an ion implantation process to form dopant regions including forming an amorphous portion in the first and second gates is performed prior to the steps of forming a first and second strained layer.

6. (original) The method of claim 5, further comprising the step of carrying out an annealing process to recrystallize the amorphous portion following the steps of forming a first and second strained layer.

7. (original) The method of claim 1, wherein the first and second stress types are selected from the group consisting of tensile stress and compressive stress formed over a respective N conductive type gate and P conductive type gate.

8. (currently amended) The method of claim 1, wherein the steps of forming a first and second strained layer comprise the steps

of:

forming the first strained layer;

removing a first portion of the first strained layer
including gate sidewall portions over one of the first and second
gates to leave an uncovered portion; and,

forming the second strained layer over the uncovered portion
including gate sidewall portions.

9. (original) The method of claim 1, wherein the first and second strained layers are deposited by a CVD process selected from the group consisting of LPCVD, ALCVD, and PECVD.

10. (original) The method of claim 1, wherein the first and second strained layers comprise a nitride.

11. (original) The method of claim 1, wherein the wherein the first and second strained layers are selected from the group consisting of silicon nitride and silicon oxynitride.

12. (original) The method of claim 1, wherein the wherein the

U.S.S.N. 10,798,960

first and second strained layers comprise a stress level up to about 2 GPa.

13. (original) The method of claim 1, wherein the first and second strained layers are formed at a thickness from about 50 Angstroms to about 1000 Angstroms.

14. (original) The method of claim 1, wherein the steps of forming the first and second strained layers is carried out at a temperature less than about 600 °C.

15. (currently amended) A method for improving charge mobility in a MOSFET device comprising the steps of:

providing a first gate with a first semiconductor conductive type and a second gate with a second semiconductor conductive type overlying a substrate;

forming a first strained dielectric layer with a first type of stress overlying said first gate;

forming a second strained dielectric layer with a second type of stress overlying said second gate;

U.S.S.N. 10,798,960

transferring the first stress type from the first strained dielectric layer to the first gate and the second stress type from the second strained dielectric layer to the second gate; and,

removing the first and second strained dielectric layers.

16. (currently amended) A method for improving charge mobility in a MOSFET device comprising the steps of:

providing a substrate comprising at least one polysilicon gate electrode;

performing an ion implantation process to form dopant regions including forming an amorphous portion in the at least one polysilicon gate electrode;

forming a first dielectric layer comprising a selected stress level selected from the group consisting of tensile stress and compressive stress over the at least one polysilicon gate electrode including gate sidewall portions without filling a gap with respect to an adjacent gate electrode; and,

carrying out an annealing process to recrystallize the amorphous portions of the respective polysilicon gate electrodes to form a stress level in the substrate.

17. (currently amended) A method for improving charge mobility in a MOSFET device comprising the steps of:

providing a substrate comprising at least one polysilicon gate electrode;

performing an ion implantation process to form dopant regions including forming an amorphous portion in the polysilicon gate electrode; and,

forming at least one dielectric layer comprising a selected stress level selected from the group consisting of tensile stress and compressive stress over the at least one polysilicon gate electrode including gate sidewall portions, said at least one dielectric layer formed without a silicide region present and without filling a gap with respect to an adjacent gate electrode.

18. (original) The method of claim 17, further comprising

carrying out an annealing process to recrystallize the amorphous portion and activate the dopant regions while forming a stress level in the substrate.

19. (original) The method of claim 17, wherein the step of forming a dielectric layer further comprises forming an underlying oxide layer.

20. (original) The method of claim 17, wherein the step of forming at least one dielectric layer comprises forming a dielectric layer in tensile stress over an N-type polysilicon gate electrode and a dielectric layer in compressive stress over a P-type polysilicon gate electrode.

21. (currently amended) The method of claim 20, comprising the steps of:

forming a first dielectric layer comprising a first stress type selected from the group consisting of tensile and compressive stress;

removing a first portion of the first dielectric layer over one of the N-type and P-type polysilicon gate electrodes

including gate sidewall portions; and,

forming a second dielectric layer comprising a second stress type opposite from the first stress type over the first portion including gate sidewall portions.

22. (original) The method of claim 17, wherein the at least one dielectric layer is formed by a CVD process selected from the group consisting of LPCVD, ALCVD, and PECVD.

23. (original) The method of claim 17, wherein the at least one dielectric layer comprises a nitride.

24. (original) The method of claim 17, wherein the at least one dielectric layer is selected from the group consisting of silicon nitride and silicon oxynitride.

25. (original) The method of claim 17, wherein the stress level is formed at up to about 2 GPa.

26. (original) The method of claim 17, wherein the at least one dielectric layer is formed at a thickness from about 50 Angstroms to about 1000 Angstroms.

U.S.S.N. 10,798,960

27. (original) The method of claim 17, further comprising the step of removing at least a portion of the least one dielectric layer.

28. (original) The method of claim 27, further comprising the step of forming a silicide region in the uppermost portion of the polysilicon gate electrode.

29. (original) The method of claim 17, wherein the step of forming the at least one dielectric layer is carried out at a temperature less than a recrystallization temperature of the amorphous portion.

30. (original) The method of claim 17, wherein the step of forming at least one dielectric layer is carried out at a temperature less than about 600 °C.

claims 31-43 cancelled

44. (new) The method of claim 1, wherein the first and second strained layers are formed without filling a gap between the first and second gate.

45. (new) The method of claim 15, wherein the first and second strained dielectric layers are formed without filling a gap between the first and second gate.

46. (new) The method of claim 15, wherein the first and second strained dielectric layers are over gate sidewall portions.

47. (new) The method of claim 1, wherein the first and second strained layers are formed without a silicide region present.

48. (new) The method of claim 15, wherein the first and second strained dielectric layers are formed without a silicide region present.

49. (new) The method of claim 16, wherein the first dielectric layer is formed without a silicide region present.